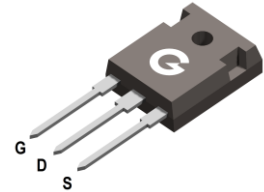
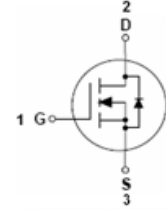


Features

- Fast switching
- Low on-resistance
- Low gate charge
- Low reverse transfer capacitances
- HBM: JESD22-A114-B: 1C

HF



TO-247

Mechanical Data

- Case: TO-247
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin-Plated Leads, Solderability-per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BL3N150U	TO-247	30 pcs / Tube	3N150

Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	1500	V
Gate-to-Source Voltage	V _{GSS}	±30	V
Continuous Drain Current (T _C = 25°C)	I _D	3	A
Continuous Drain Current (T _C = 100°C)		1.9	A
Pulsed Drain Current (t _p = 10μs, T _C = 25°C)	I _{DM}	12	A
Single Pulse Avalanche Energy ^{1,2}	E _{AS}	30	mJ
Power Dissipation (T _C = 25°C)	P _D	200	W
Operating Junction Temperature Range	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case	R _{θJC}	-	-	0.62	°C/W
Thermal Resistance Junction-to-Air	R _{θJA}	-	-	40	°C/W

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	1500	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 1500V, V_{GS} = 0V$	-	-	25	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	± 100	nA
On Characteristics						
$R_{DS(ON)}$	Drain-Source On-resistance ^{*1}	$V_{GS} = 10V, I_D = 1.5A$	-	5.5	8	Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5	3.5	5	V
R_G	Gate Resistance	$V_{GS} = 0V, f = 1MHz$	-	2	-	Ω
Dynamic Characteristics						
C_{ISS}	Input Capacitance	$V_{GS} = 0V$	-	1728	-	pF
C_{OSS}	Output Capacitance	$V_{DS} = 25V$	-	101	-	
C_{RSS}	Reverse Transfer Capacitance	$f = 1.0MHz$	-	8.9	-	
Switching Characteristics						
$t_{d(ON)}$	Turn-on Delay Time ^{*3}	$V_{DD} = 750V$ $V_{GS} = 10V$ $I_D = 3A$ $R_G = 4.7\Omega$	-	25	-	ns
t_r	Turn-on Rise Time ^{*3}		-	48	-	
$t_{d(OFF)}$	Turn-Off Delay Time ^{*3}		-	57	-	
t_f	Turn-Off Fall Time ^{*3}		-	52	-	
Q_G	Total Gate-Charge	$V_{DD} = 960V$	-	45	-	nC
Q_{GS}	Gate to Source Charge	$V_{GS} = 10V$	-	7.5	-	
Q_{GD}	Gate to Drain ("Miller") Charge	$I_D = 3A$	-	21.2	-	
Source-Drain Diode Characteristics						
V_{SD}	Diode Forward Voltage ^{*1}	$I_{SD} = 3A, V_{GS} = 0V$	-	0.8	1.5	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F = 1.5A, V_R = 100V$	-	1	-	μs
Q_{rr}	Body Diode Reverse Recovery Charge	$di/dt = 100A/\mu s$	-	6.6	-	μC

Notes:

1. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
2. The E_{AS} data shows Max. rating. The test condition is $V_{DD} = 50V, V_{GS} = 15V, L = 10mH$
3. Guaranteed by design, not subject to production

Ratings and Characteristic Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

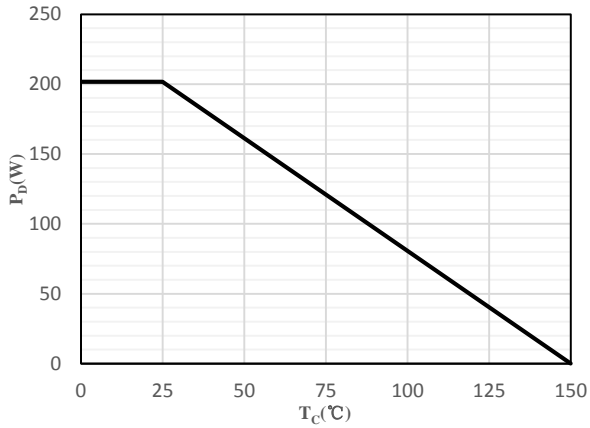


Fig 1 Power Dissipation

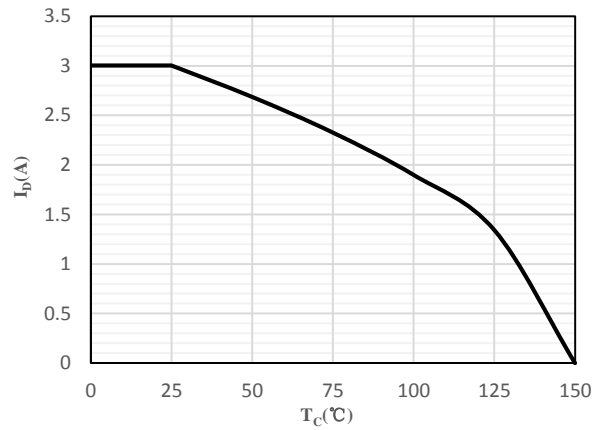


Fig 2 Drain Current

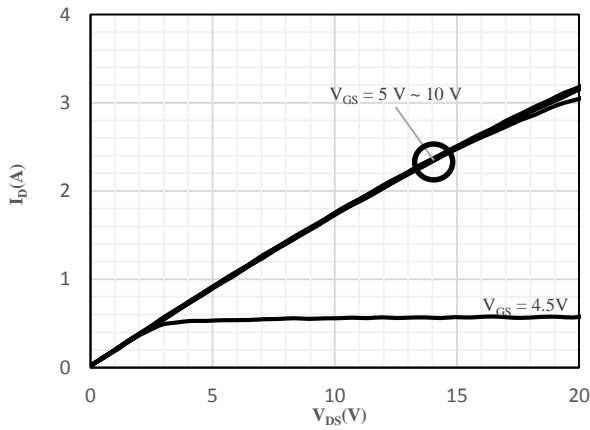


Fig 3 Typical Output Characteristics

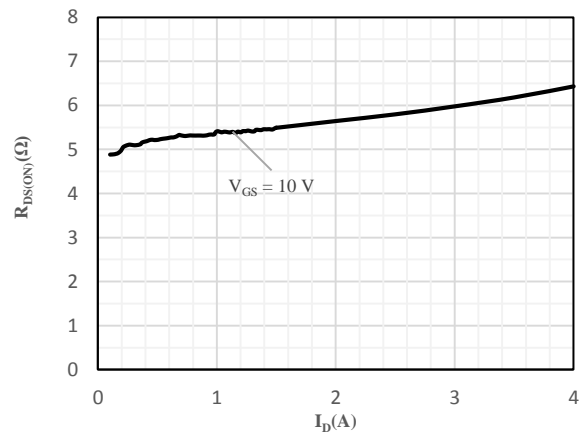


Fig 4 On-Resistance vs. Drain Current and Gate Voltage

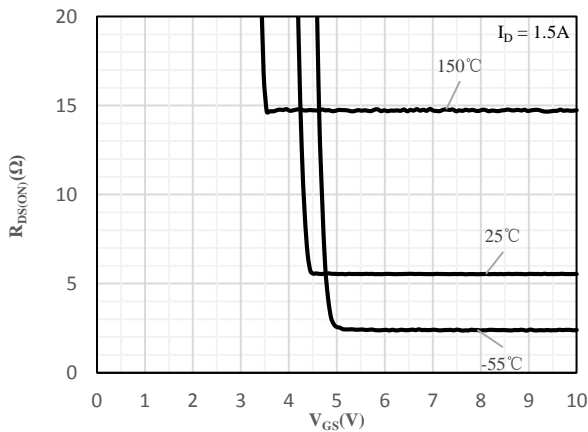


Fig 5 On-Resistance vs. Gate-Source Voltage

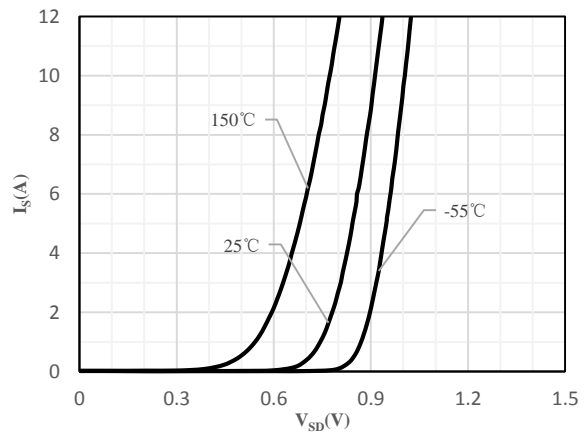


Fig 6 Body-Diode Characteristics

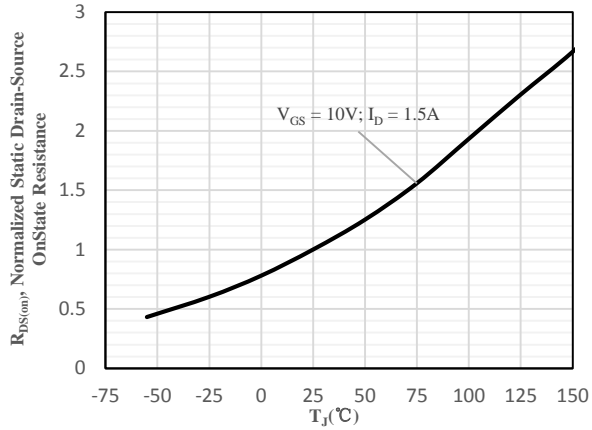


Fig 7 Normalized On-Resistance vs. Junction Temperature

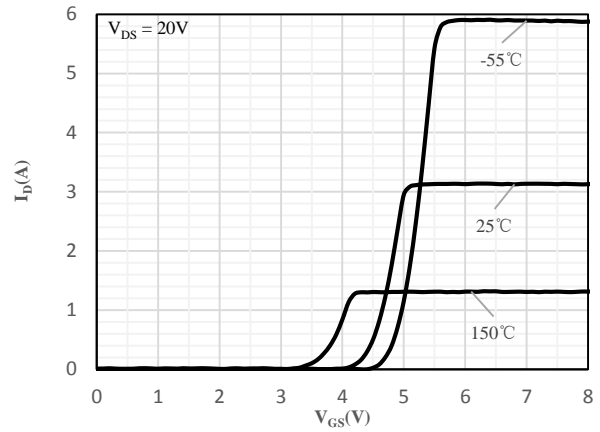


Fig 8 Transfer Characteristics

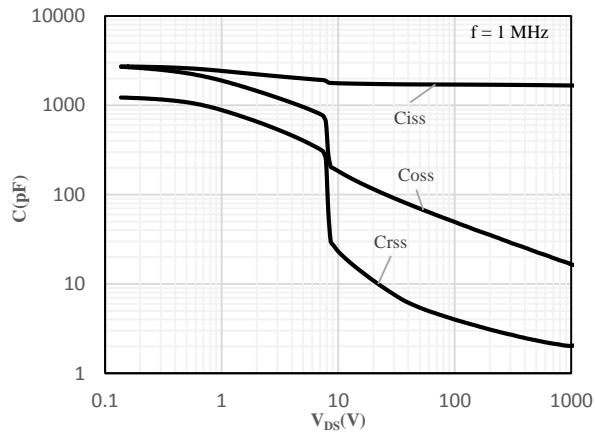


Fig 9 Capacitance Characteristics

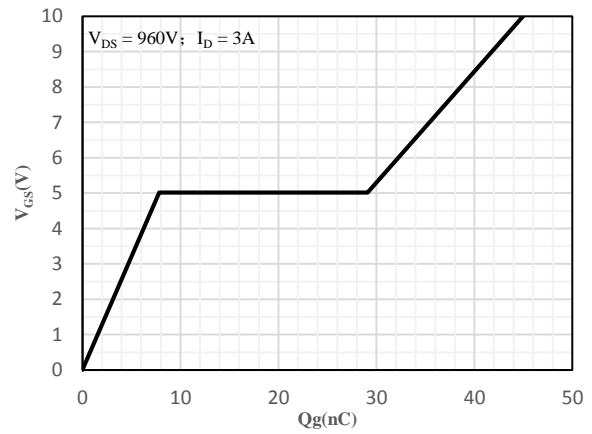


Fig 10 Gate-Charge Characteristics

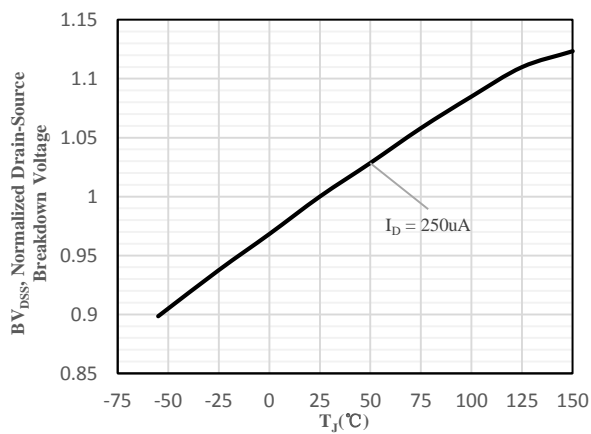


Fig 11 Normalized Breakdown Voltage vs. Junction Temperature

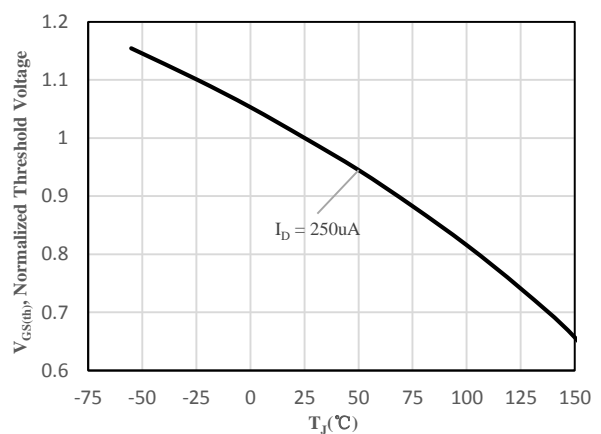
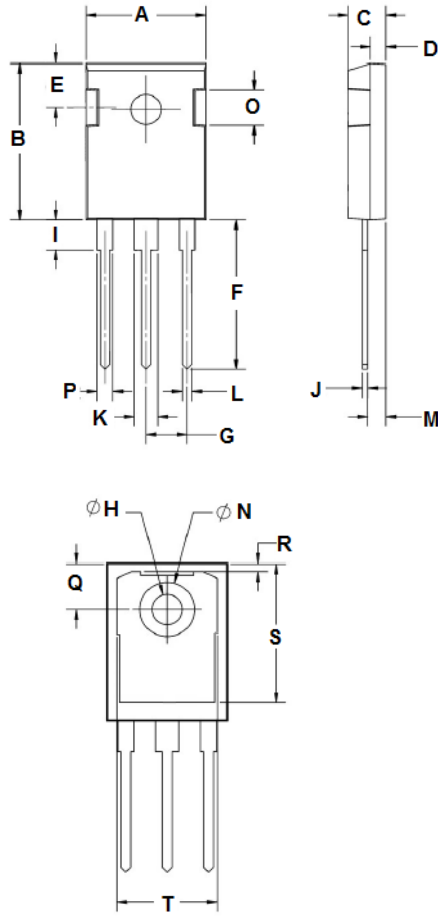


Fig 12 Normalized $V_{GS(th)}$ vs. Junction Temperature

Package Outline Dimensions (Unit: mm)



TO-247		
Dimension	Min.	Max.
A	15.50	16.10
B	20.70	21.30
C	4.70	5.30
D	1.80	2.20
E	5.20	5.80
F	19.70	20.30
G	5.20	5.60
H	3.30	3.70
I	3.90	4.30
J	0.50	0.70
K	2.80	3.20
L	1.00	1.40
M	2.20	2.60
N	7.00	7.20
O	4.90	5.30
P	1.80	2.20
Q	5.70	5.90
R	0.80	1.20
S	17.00	17.80
T	13.60	14.20

IMPORTANT NOTICE

Changzhou Galaxy Century Microelectronics (GME) reserves the right to make changes without further notice to any product information (copyrighted) herein to make corrections, modifications, improvements, or other changes. GME does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others.